BC807-25W, BC807-40W

General Purpose Transistors

PNP Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	-45	V
Collector – Base Voltage	V _{CBO}	-50	V
Emitter – Base Voltage	V _{EBO}	-5.0	V
Collector Current – Continuous	Ic	-500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C	P _D	460	mW
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	272	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

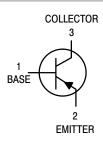
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 Board, 1 oz. Cu, 100 mm².



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SC-70 CASE 419 STYLE 3

MARKING DIAGRAM



5x = Device Code x = B or C

M = Date Code*

■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

BC807-25W, BC807-40W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS				•		
Collector – Emitter Breakdown Voltage (I _C = –10 mA)		V _{(BR)CEO}	-45	-	-	V
Collector – Emitter Breakdown Voltage (V _{EB} = 0, I _C = –10 μA)		V _{(BR)CES}	-50	-	-	V
Emitter – Base Breakdown Voltage ($I_E = -1.0 \mu A$)		V _{(BR)EBO}	-5.0	-	-	V
Collector Cutoff Current $(V_{CB} = -20 \text{ V})$ $(V_{CB} = -20 \text{ V}, T_J = 150^{\circ}\text{C})$		Ісво	_ _	_ _	-100 -5.0	nA μA
ON CHARACTERISTICS						
DC Current Gain $(I_C = -100 \text{ mA}, V_{CE} = -1.0 \text{ V})$ $(I_C = -500 \text{ mA}, V_{CE} = -1.0 \text{ V})$	BC807-25, SBC807-25 BC807-40, SBC807-40	h _{FE}	160 250 40	- - -	400 600 –	-
Collector – Emitter Saturation Voltage (I _C = -500 mA, I _B = -50 mA)		V _{CE(sat)}	_	-	-0.7	V
Base – Emitter On Voltage ($I_C = -500 \text{ mA}, V_{CE} = -1.0 \text{ V}$)		V _{BE(on)}	_	-	-1.2	V
SMALL-SIGNAL CHARACTERISTICS			-	•	-	
Current – Gain – Bandwidth Product ($I_C = -10$ mA, $V_{CE} = -5.0$ Vdc, $f = 100$ MHz)		f _T	100	-	-	MHz
Output Capacitance (V _{CB} = -10 V, f = 1.0 MHz)		C _{obo}	-	10	_	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Specific Marking	Package	Shipping †	
BC807-25WT1G			2000 / Tana & Baal	
SBC807-25T1G*	5B	SC-70 (Pb-Free)	3000 / Tape & Reel	
BC807-25WT3G		(' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	10,000 / Tape & Reel	
BC807-40WT1G		SC-70 3000 / Tape (Pb-Free)		
SBC807-40WT1G*	5C			
BC807-40WT3G		(' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	10,000 / Tape & Reel	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP

AS Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

TYPICAL CHARACTERISTICS - BC807-25W, SBC807-25W

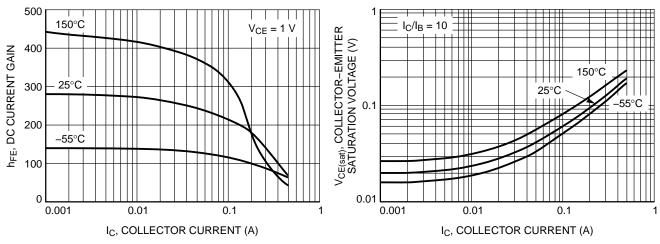


Figure 1. DC Current Gain vs. Collector Current

Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

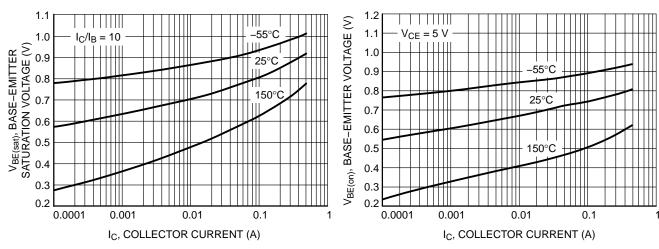


Figure 3. Base Emitter Saturation Voltage vs.
Collector Current

Figure 4. Base Emitter Voltage vs. Collector Current

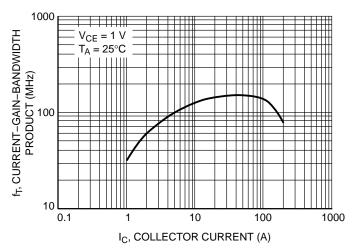


Figure 5. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC807-25W, SBC807-25W

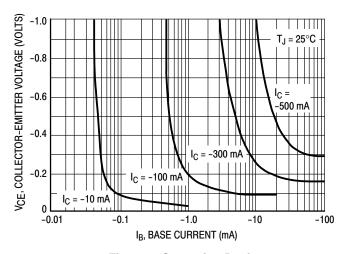


Figure 6. Saturation Region

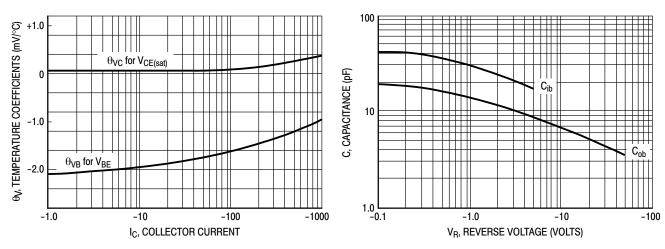


Figure 7. Temperature Coefficients

Figure 8. Capacitances

BC807-25W, BC807-40W

TYPICAL CHARACTERISTICS - BC807-40W, SBC807-40W

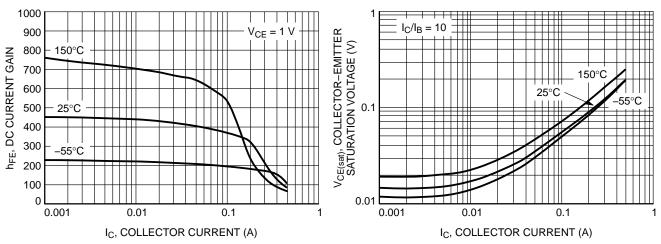


Figure 9. DC Current Gain vs. Collector Current

Figure 10. Collector Emitter Saturation Voltage vs. Collector Current

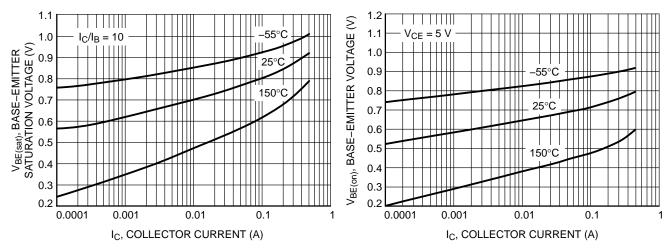


Figure 11. Base Emitter Saturation Voltage vs.
Collector Current

Figure 12. Base Emitter Voltage vs. Collector
Current

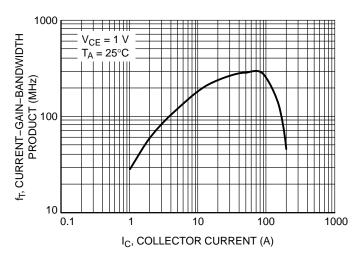


Figure 13. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC807-40W, SBC807-40W

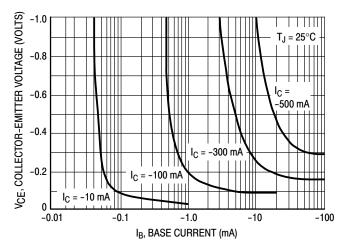


Figure 14. Saturation Region

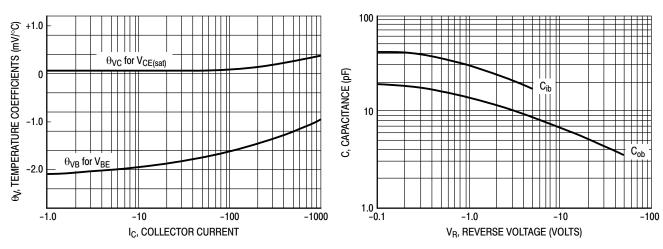


Figure 15. Temperature Coefficients

Figure 16. Capacitances

TYPICAL CHARACTERISTICS - BC807-25W, SBC807-25W, BC807-40W, SBC807-40W

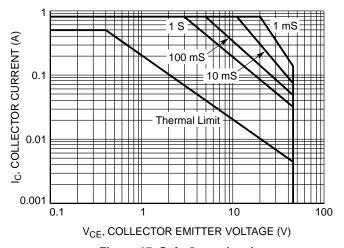


Figure 17. Safe Operating Area

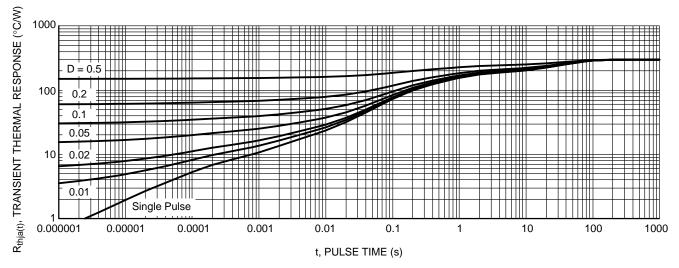
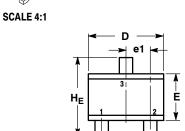


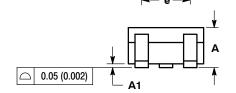
Figure 18. Thermal Response

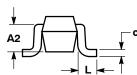


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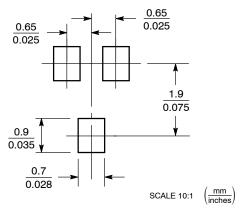
DATE 11 NOV 2008







SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	MOM	MAX
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF 0.028 REF				
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC MARKING DIAGRAM



XX = Specific Device Code

Μ = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	CATHODE
COLLECTOR	COLLECTOR	3. DRAIN	CATHODE-ANODE	3. ANODE-CATHODE	CATHODE

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